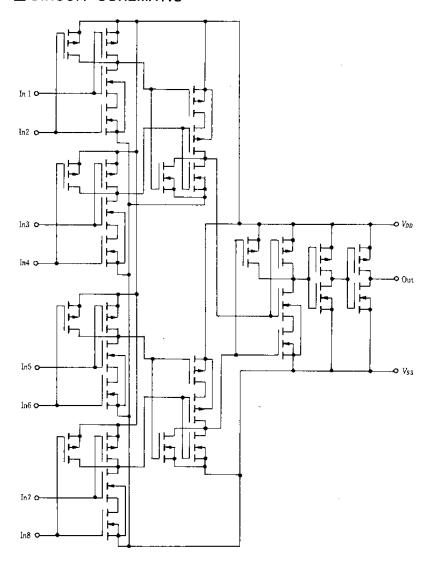
HD14068B

8-input NAND Gate

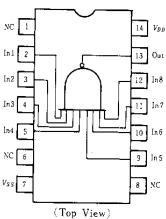
■ FEATURES

- Quiescent Current = 0.5nA typ/pkg @5V
- Noise Immunity = 45% of V_{DD} typ
 Capable of Driving One Low-power Schottky TTL Load Over the Rated Temperature Range
- Pin-for Pin Replacements for CD4068B and MC14068B Series

■ CIRCUIT SCHEMATIC



■PIN ARRANGEMENT



■ ELECTRICAL CHARACTERISTICS

Characteristic	Symbol		Test Conditions			25℃		85 ℃		• • •	
Symoon		$V_{DB}(V)$ lest Conditions		min	max	min	typ	max	min	max	Unit
Output Voltage		5.0	$V_{in} = V_{DD}$		0.05	_	0	0.05		0.05	v
	Vol	10			0.05	-	0	0.05	_	0.05	
		15		_	0.05	_	0	0.05		0.05	
Carpar Formage		5.0	$V_{in}=0$	4.95		4.95	5.0		4.95		v
	Von	10		9.95		9.95	10	_	9.95		
·	İ	15		14.95	_	14.95	15		14.95		
		5.0	$V_{out} = 4.5 \text{V}$	7 -	1.5	_	2.25	1.5	-	1.5	V
	V_{IL}	10	V 9.0V		3.0		4.50	3.0	_	3.0	
Input Voltage	L	15	$V_{out} = 13.5 \text{V}$		4.0		6.75	4.0	_	4.0	
Input Voltage		5.0	$V_{out} = 0.5 \text{V}$	3.5	_	3.5	2.75	_	3.5	_	v
	V_{IH}	10	$V_{out} = 1.0 \text{V}$	7.0	_	7.0	5.50	-	7.0	_	
		15	$V_{out} = 1.5 \text{V}$	11.0	_	11.0	8.25		11.0		
	:	5.0	$V_{OH} = 2.5 \text{V}$	-2.5	_	-2.1	-4.2		-1.7		mA
	Іон	5.0	$V_{OH} = 4.6 \text{V}$	-0.52		-0.44	-0.88	_	-0.36		
	; 10H	10	$V_{OH} = 9.5 \text{V}$	-1.3	_	-1.1	-2.25		-0.9		
Output Drive Current		15	$V_{OH} = 13.5 \mathrm{V}$	-3.6		-3.0	-8.8	_	-2.4		
	Iot	5.0	$V_{\text{GL}} = 0.4 \text{V}$	0.52		0.44	0.88	_	0.36	_	
		10	$V_{OL} = 0.5 \mathrm{V}$	1.3	_	1.1	2.25		0.9		mA
:	:	15	$V_{GL} = 1.5 \text{V}$	3.6		3.0	8.8	-	2.4	_	
Input Current	I_{cr}	15			±0.3	_	±0.00001,	±0.3		±1.0	μΑ
Input Capacitance	C,,,		$V_{i,n}=0$	· - i	_	-	5.0	7.5	_	_	рF
Quiescent Current	I_{DD}	5.0	Zero Signal, per Package	i -	1.0		0.0005	1.0	_	7.5	
		10			2.0	_	0.0010	2.0	_	15.0	μΑ
		15			4.0	_	0.0015	4.0		30.0	
·		5.0	Dynamic + I_{DD} , $C_L = 50 \text{pF}$, $f = 1 \text{ kHz}$			-	0.3	- 1	_		μΑ
Total Supply Current*	$I_{\mathcal{T}}$	10		_	_	_	0.6		_		
		15					0.9		_		

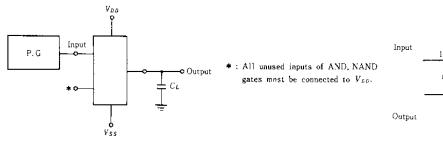
 $[\]ensuremath{\bigstar}$ To calculate total supply current at frequency other than IkHz.

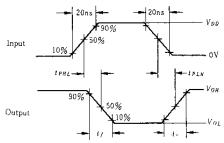
 $@V_{00} = 5.0 \text{V} \\ I_7 = (0.3 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.6 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 15 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ @V_{00} = 10 \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\ \text{V} \\ I_7 = (0.9 \, \mu\text{A/kHz}) \\ f + I_{00} \\$

ESWITCHING CHARACTERISTICS ($C_L = 50 \text{pF}$, $Ta = 25^{\circ}\text{C}$)

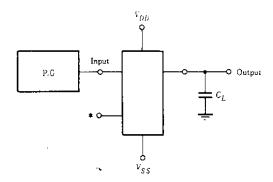
Characteristic	Symbol	$V_{DD}(V)$	min	typ	max	Unit
Output Rise Time	t,	5.0	_	100	200	ns
		10	7901	50	100	
		15	_	40	80	
Output Fall Time	t,	5.0	_	100	200	ns
		10		50	100	
		15		40	80	
Propagation Delay Time	t _{PLH}	5.0		200	400	ns
		10		80	160	
		15		60	120	
	t PH L	5.0		200	400	
		10		80	160	ns
		15	****	60	120	7

SWITCHING TIME TEST CIRCUIT

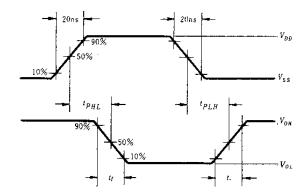




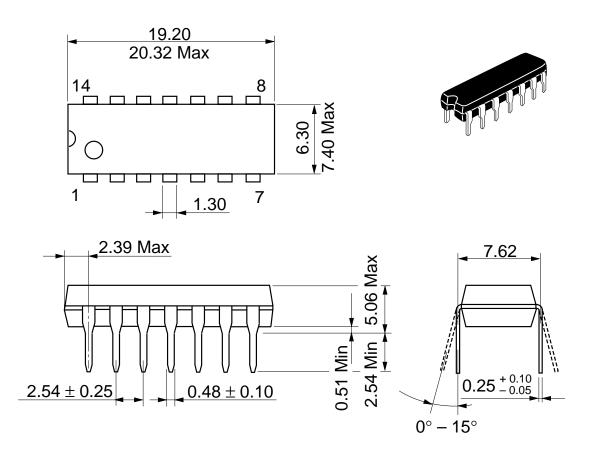
SWITCHING TIME TEST CIRCUIT



* All unused inputs of AND, NAND gates must be connected to $V_{\it OD}$.

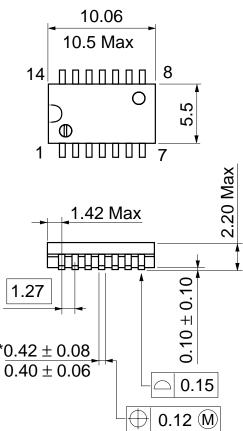


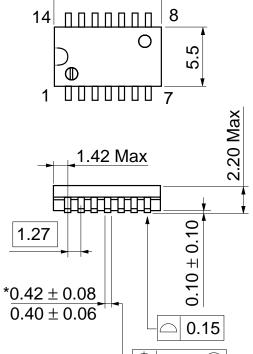
Unit: mm



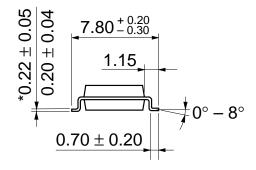
Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.97 g

Unit: mm





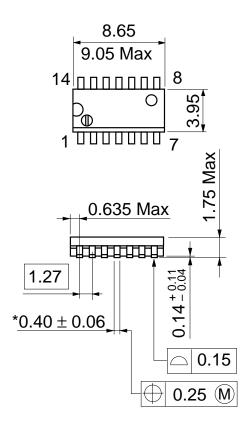




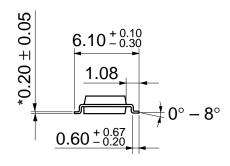
Hitachi Code	FP-14DA
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.23 g

Dimension	including	the	plating	thickness
Bas	se materia	al dir	mensioi	1

Unit: mm







Hitachi Coo	de	FP-14DN	
JEDEC		Conforms	
EIAJ		Conforms	
Weight (refe	erence value)	0.13 g	

*Pd plating

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